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| APPLICATION NO. FILING DATE | | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. | |
|--|---------------|----------------------|-------------------------|------------------|--|
| 10/790,339 | 03/01/2004 | David W. Sherrer | R&H 04-02CIP 9391 | | |
| 75 | 90 05/18/2005 | | EXAMINER | | |
| JONATHAN D. BASKIN | | | HO, TU TU V | | |
| EDWARDS & ANGELL, LLP P. O. BOX 55874 | | | ART UNIT | PAPER NUMBER | |
| BOSTON, MA 02205 | | | 2818 | | |
| | | | DATE MAILED: 05/18/2005 | | |

Please find below and/or attached an Office communication concerning this application or proceeding.

| | | Application | on No. | Applicant(s) | | | | |
|--|--|---|--|---|--------|--|--|--|
| Office Action Summary | | 10/790,33 | 9 | SHERRER, DAVID W. | | | | |
| | | Examiner | | Art Unit | | | | |
| | | Tu-Tu Ho | | 2818 | | | | |
| The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply | | | | | | | | |
| THE - Exte after - If the - If NO - Failt Any | ORTENED STATUTORY PERIOD FOR REP MAILING DATE OF THIS COMMUNICATION nsions of time may be available under the provisions of 37 CFR 1 SIX (6) MONTHS from the mailing date of this communication. e period for reply specified above is less than thirty (30) days, a rep period for reply is specified above, the maximum statutory perion to reply within the set or extended period for reply will, by staturely received by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b). | 1.136(a). In no eve ply within the statu d will apply and wi utė, cause the appl | ent, however, may a reply be tim story minimum of thirty (30) day: Il expire SIX (6) MONTHS from ication to become ABANDONE | nely filed s will be considered timely. the mailing date of this communic D (35 U.S.C. § 133). | ation. | | | |
| Status | | | | | | | | |
| 1) 又 | Responsive to communication(s) filed on <u>01</u> | March 2004. | • | | | | | |
| • — | This action is FINAL . 2b)⊠ This action is non-final. | | | | | | | |
| 3)□ | Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. | | | | | | | |
| Disposit | ion of Claims | | | | | | | |
| 5)□ 6)⊠ 7)□ | Claim(s) 1-20 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. Claim(s) is/are allowed. Claim(s) 1-20 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restriction and/or election requirement. | | | | | | | |
| Applicat | ion Papers | | | | | | | |
| 10) | The specification is objected to by the Examination The drawing(s) filed on is/are: a) and applicant may not request that any objection to the Replacement drawing sheet(s) including the correct The oath or declaration is objected to by the | ccepted or b) ne drawing(s) bection is requir | e held in abeyance. See ed if the drawing(s) is ob | e 37 CFR 1.85(a). jected to. See 37 CFR 1.1 | | | | |
| Priority | under 35 U.S.C. § 119 | | | | | | | |
| 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some col None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. | | | | | | | | |
| 2) Notion Notion Notion | ot(s) Dee of References Cited (PTO-892) Dee of Draftsperson's Patent Drawing Review (PTO-948) The mation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 The results of the statement of the statem | 98) . | 4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other: | | ı | | | |

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DETAILED ACTION

Oath/Declaration

1. The oath/declaration filed on 03/01/2004 is acceptable.

Double Patenting

2. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321(c) may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1-20 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-36 of U.S. Patent No. 6,698,295 (the '295 patent). Although the conflicting claims are not identical, they are not patentably distinct from each other. Claims 1-20 of the present invention is a similar version of the claimed invention in claims 1-36 of the above-identified U.S. Patent with similar intended scope.

With respect to claims 10, 19, and 20, although the claims of the '295 patent does not disclose silicon carbide as a material for the dielectric layer, the use of silicon carbide for the

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dielectric layer was known at the time the invention was made. The difference in materials between the claims of the '295 patent and the present claims is silicon nitride and silicon carbide. Busta et al. U.S. Patent 6,140,646, in also disclosing a microstructure including micro-cantilever 245 (Fig. 1) comprising a dielectric layer 228 and conductive layer 234/240, disclose that the dielectric layer 228 could be silicon nitride or silicon carbide (column 4, lines 28-31), thereby teaching that the two materials are art equivalents. Therefore, it would have been obvious to one of ordinary skill in the art the time the invention was made to form the dielectric layer of the present claims using silicon carbide rather than silicon nitride, because the two materials are art equivalents.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

(e) the invention was described in

(1) an application for patent, published under section 122(b), by another filed in the United States before the

invention by the applicant for patent or

Claims 11-12 and 17-20 are rejected under 35 U.S.C. 102(e) as being anticipated by 3. Busta et al. U.S. Patent 6,140,646 (the '646 reference).

The '646 reference discloses in the figures, particularly Fig. 1, and respective portions of the specification a micromachined apparatus as claimed.

Referring to claim 11, the reference discloses a micromachined apparatus comprising: a substrate (200); and

⁽²⁾ a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

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a released microstructure (245) disposed on the substrate, comprising:

a dielectric layer (228, column 4, lines 15-31)), and

a conductive layer (234) attached to the dielectric layer, wherein the conductive layer has a thickness less than 1/5 the dielectric layer thickness (column 7, lines 32-39, thickness of the dielectric layer 228 is about 2500 to 10000 angstroms, and column 8, lines 1-10, the thickness for the conductive layer 234 is about 400 angstroms).

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Referring to claims 17, 19, and 20, and using the same reference characters and citations as detailed above, the reference discloses a micromachined apparatus comprising:

a substrate; and

a released cantilever disposed on the substrate, comprising:

a silicon carbide dielectric layer, and

a conductive layer attached to the dielectric layer, wherein the conductive layer has a thickness less than 1/5 the dielectric layer thickness.

Referring to claim 12, as can be seen from Fig. 1, the conductive layer (234) contacts and covers the dielectric layer (228).

Referring to claim 18, the reference further discloses that the microstructure comprises a switch (column 3, lines 43-64).

Conclusion

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am - 5:00 pm.

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supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone number for the

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent

Application Information Retrieval (PAIR) system. Status information for published applications

may be obtained from either Private PAIR or Public PAIR. Status information for unpublished

applications is available through Private PAIR only. For more information about the PAIR

system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR

system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Tu-Tu Ho

May 14, 2005